

Andrew J Green

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Thermally-Aware Layout Design of $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ Lateral MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1251-1257.	3.0	11
2	Al_2O_3 -Gallium oxide power electronics. APL Materials, 2022, 10, .	5.1	184
3	Scaled T-Gate $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ MESFETs With 2.45 kV Breakdown and High Switching Figure of Merit. IEEE Electron Device Letters, 2022, 43, 1307-1310.	3.9	8
4	Electrical and chemical analysis of Ti/Au contacts to $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$. APL Materials, 2021, 9, 061104.	5.1	23
5	The effectiveness of heat extraction by the drain metal contact of Al_2O_3 MOSFETs. , 2021, , .		1
6	Homoepitaxial $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ transparent conducting oxide with conductivity $\sigma = 2323 \text{ S cm}^{-1}$. APL Materials, 2021, 9, .	5.1	22
7	Lateral $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	2.0	85
8	RF Power Performance of Sc(Al,Ga)N/GaN HEMTs at Ka-Band. IEEE Electron Device Letters, 2020, 41, 1181-1184.	3.9	41
9	Thin channel $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ MOSFETs with self-aligned refractory metal gates. Applied Physics Express, 2019, 12, 126501.	2.4	35
10	ScAlN/GaN High-Electron-Mobility Transistors With 2.4-A/mm Current Density and 0.67-S/mm Transconductance. IEEE Electron Device Letters, 2019, 40, 1056-1059.	3.9	63
11	Recessed-Gate Enhancement-Mode $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ MOSFETs. IEEE Electron Device Letters, 2018, 39, 67-70.	3.9	187
12	Si content variation and influence of deposition atmosphere in homoepitaxial Si-doped $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ films by pulsed laser deposition. APL Materials, 2018, 6, 101102.	5.1	40
13	High pulsed current density $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ MOSFETs verified by an analytical model corrected for interface charge. Applied Physics Letters, 2017, 110, .	3.3	75
14	Highly conductive homoepitaxial Si-doped Al_2O_3 films on (010) Al_2O_3 by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	128
15	Enhancement-mode Al_2O_3 wrap-gate fin field-effect transistors on native (100) Al_2O_3 substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	3.3	298
16	Ionic Metal-Oxide TFTs for Integrated Switching Applications. IEEE Transactions on Electron Devices, 2016, 63, 1921-1927.	3.0	9
17	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3$ MOSFETs. IEEE Electron Device Letters, 2016, 37, 902-905.	3.9	468